

General Description

The WSD2209DN is the highest performance trench P-ch MOSFETs with extreme high cell density, which provide excellent R_{DS(on)} and gate charge for most of the synchronous buck converter applications.

The WSD2209 meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

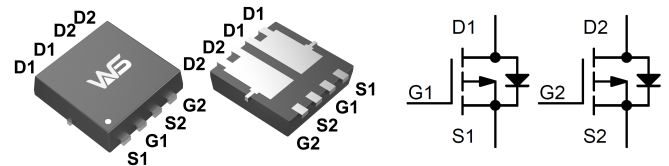
Product Summary

BVDSS	R _{DS(on)}	I _D
-20V	33mΩ	-7.5A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

DFN3X3-8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		10s	Steady State	
V _{DS}	Drain-Source Voltage	-20		V
V _{GS}	Gate-Source Voltage	± 10		V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ -10V ¹	-7.5		A
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ -10V ¹	-4.5		A
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ -10V ¹	-36	-30	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ -10V ¹	-28	-23	A
I _{DM}	Pulsed Drain Current ²	-25		A
EAS	Single Pulse Avalanche Energy ³	---		mJ
I _{AS}	Avalanche Current	---		A
P _D @T _C =25°C	Total Power Dissipation ⁴	2.5		W
P _D @T _A =25°C	Total Power Dissipation ⁴	1.6	1.7	W
T _{STG}	Storage Temperature Range	-55 to 150		°C
T _J	Operating Junction Temperature Range	-55 to 150		°C

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-20	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=-1\text{mA}$	---	-0.132	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-4.5V, I_D=-4A$	---	28	33	m Ω
		$V_{GS}=-2.5V, I_D=-3A$	---	37	45	
		$V_{GS}=-1.8V, I_D=-2A$	---	50	68	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-0.3	-0.6	-1	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.4	---	mV/ $^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-20V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-20V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 8V, V_{DS}=0V$	---	10	---	μA
gfs	Forward Transconductance	$V_{DS}=-5V, I_D=-20A$	---	9	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	3	---	Ω
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-10V, V_{GS}=-4.5V, I_D=-8A$	---	13.8	17.94	nC
Q_{gs}	Gate-Source Charge		---	4.1	5.33	
Q_{gd}	Gate-Drain Charge		---	5.6	7.28	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-10V, V_{GS}=-4.5V, R_G=3\Omega, I_D=-1A, R_L=0.5\Omega$	---	6.2	---	ns
T_r	Rise Time		---	12.7	---	
$T_{d(off)}$	Turn-Off Delay Time		---	51.7	---	
T_f	Fall Time		---	16	---	
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1\text{MHz}$	---	1160	---	pF
C_{oss}	Output Capacitance		---	104	---	
C_{rss}	Reverse Transfer Capacitance		---	29	---	

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, $t \leq 10\text{sec}$.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

Typical Characteristics

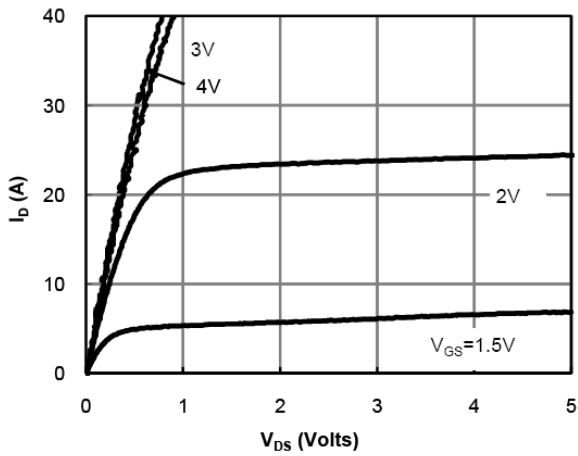


Fig 1: On-Region Characteristics

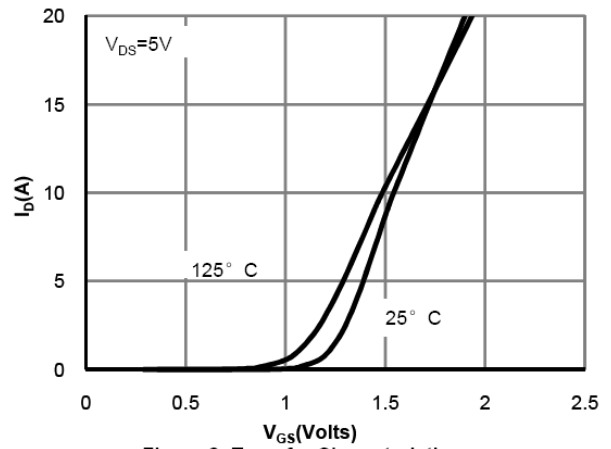


Figure 2: Transfer Characteristics

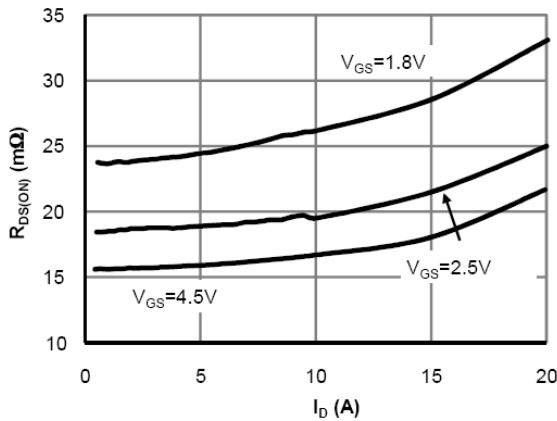


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

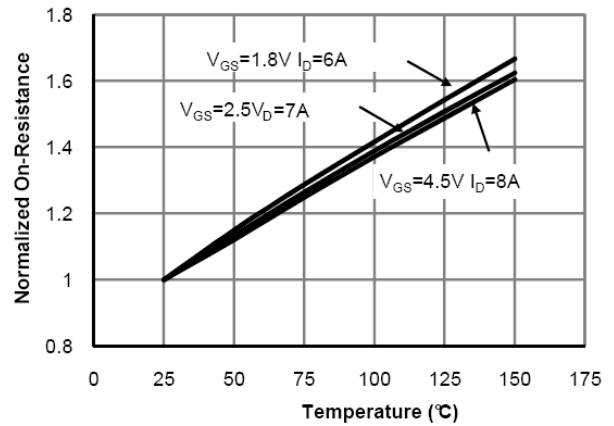


Figure 4: On-Resistance vs. Junction Temperature

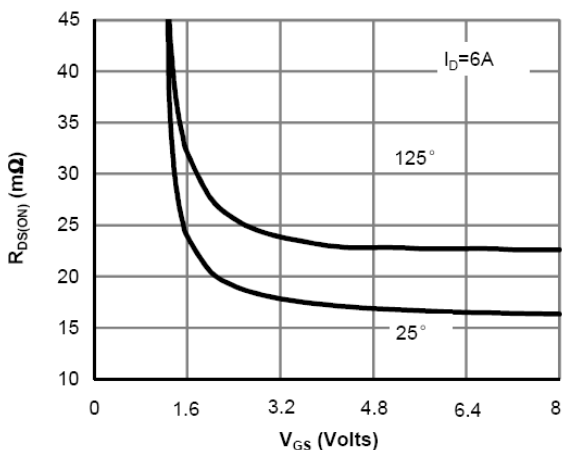


Figure 5: On-Resistance vs. Gate-Source Voltage

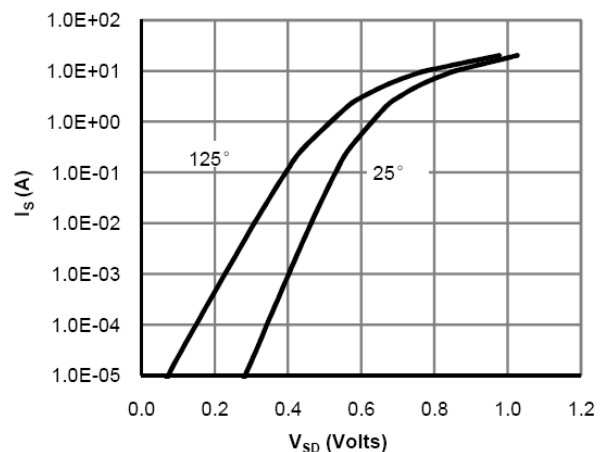


Figure 6: Body-Diode Characteristics

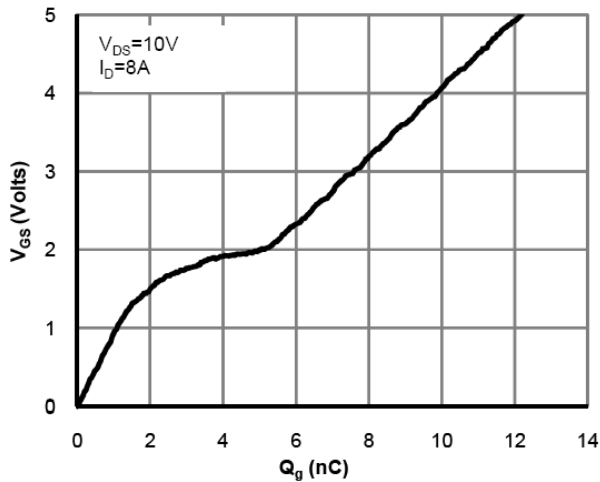


Figure 7: Gate-Charge Characteristics

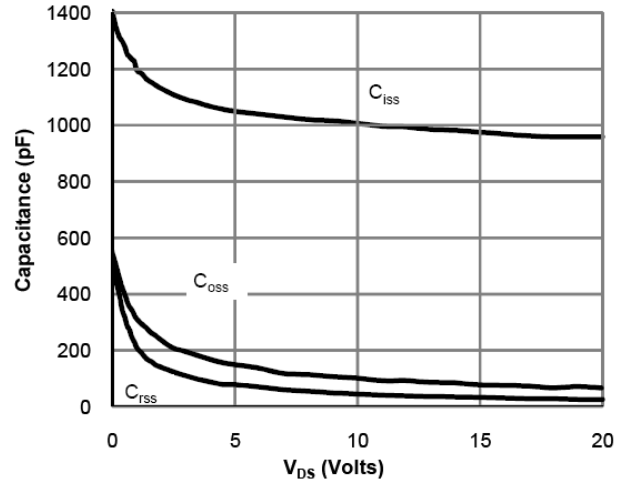


Figure 8: Capacitance Characteristics

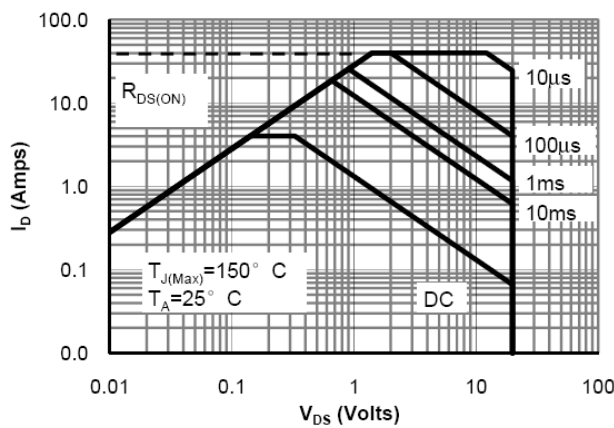


Figure 9: Maximum Forward Biased Safe Operating Area

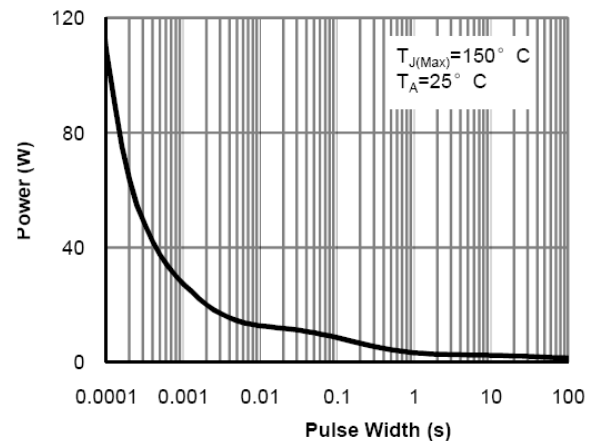


Figure 10: Single Pulse Power Rating Junction-to-Case

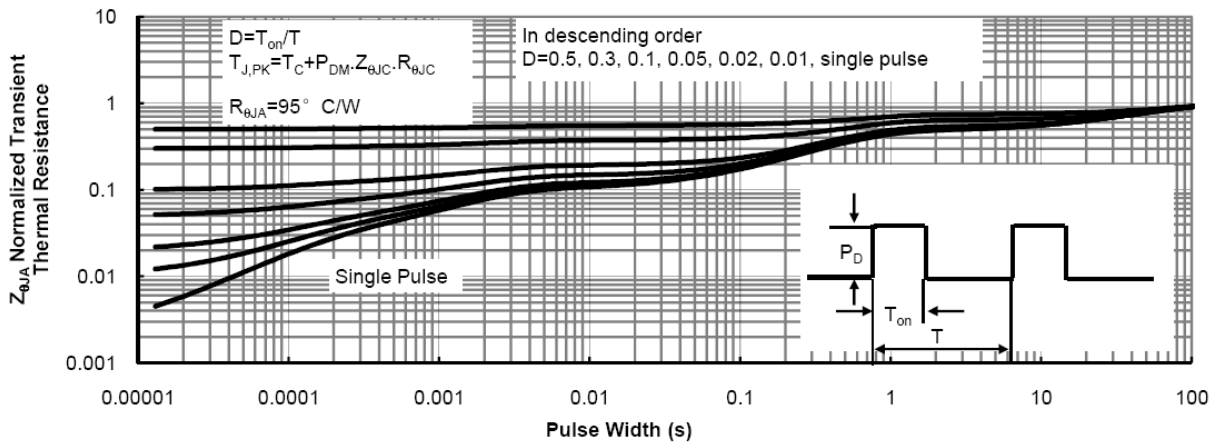


Figure 11: Normalized Maximum Transient Thermal Impedance

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